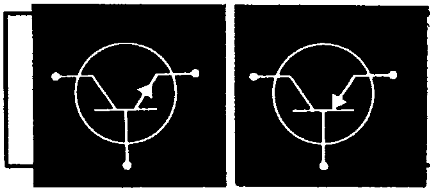


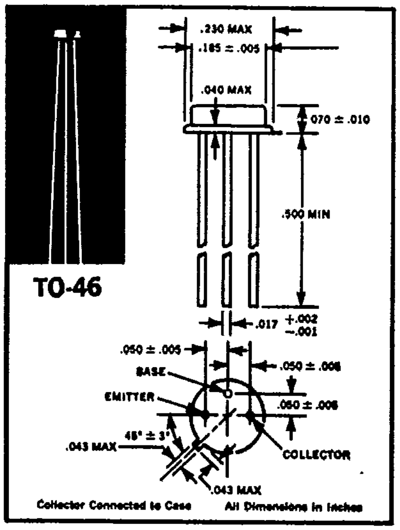
ULTRA LOWr_{EC} (sat)
SILICON EPITAXIAL JUNCTION PNP/NPN SWITCHING TRANSISTORS

2N3677
2N5066

GEOMETRY 292, (2N3677)
GEOMETRY 485, (2N5066)

T-37-23
T-35-23

- COMPLEMENTARY TYPES 2N3677 (PNP) 2N5066(NPN)
- r_{EC} (sat) 4 Ohms TYPICAL
- LOW C_{eb}
- LOW LEAKAGE
- HIGH BV_{EBO}



ELECTRICAL DATA ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	2N3677/2N5066	UNITS
Collector to Emitter Voltage	BV_{CES}	20	Volts
Emitter to Collector Voltage	BV_{ECS}	20	Volts
Collector to Base Voltage	BV_{CBO}	30	Volts
Emitter to Base Voltage	BV_{EBO}	30	Volts
Collector Current	I_C	100	mA
Power Dissipation	P_C	400	mW
Derating Factor	D_F	2.3	mW/°C
Junction Temperature (operating and storage)	T_J	−65°C to +200°C	
Lead Temperature (1/16″ ± 1/32″ from case)	T_L	240°C for 10 sec.	

ELECTRICAL CHARACTERISTICS: TA = 25°C (UNLESS OTHERWISE STATED)

PARAMETER	SYMBOL	CONDITION	2N3677/2N5066 Min.	Typ.	Max.	UNITS
Collector To Base Leakage	I_{CBO}	$V_{CB} = V_{CB}$MAX.	—	0.5	1.0	nA
Emitter to Base Leakage	I_{EBO}	$V_{EB} = V_{EB}$MAX.	—	0.5	1.0	nA
Collector To Base Leakage	I_{CBO}	$V_{CB} = V_{CB}$MAX. (TEMP = 100°C)	—	30	100	nA
Emitter To Base Leakage	I_{EBO}	$V_{EB} = V_{EB}$MAX. (TEMP = 100°C)	—	30	100	nA
Offset Voltage	V_O	$I_B = 1mA$ $I_E = 0$	—	0.7	1.0	mV
DC Common Collector Forward Current Transfer Ratio	h_{FC}	$V_{EC} = 6V$ $I_E = 1mA$	4	8	—	—
High Frequency Current Gain	h_{fe}	$V_{CE} = 6V$, $I_C = 1mA$ f = 1MC	5	10	—	—
Inverted Dynamic Saturation Resistance	r_{EC}(sat)	$I_e = 0.1mA$ $I_B = 1.0mA$ f = 1kHz	—	4	8	Ohms
Collector To Base Capacitance	C_{ob}	$V_{CB} = 6V$, $I_E = 0$, f = 159kHz	—	6	10	pfd
Emitter To Base Capacitance	C_{eb}	$V_{EB} = 6V$, $I_C = 0$, f = 159kHz	—	5	6	pfd

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